

Autonomous, ISO 9001:2015 & QS I-Gauge Diamond Rated Institute, Accredited by NAAC with 'A++' Grade NBA Accreditation for CE, EEE, ME, ECE, CSE, EIE, IT B.Tech. Programmes Approved by AICTE, New Delhi, Affiliated to JNTUH, NIRF 109 Rank in engineering Category Recognized as "College with Potential for Excellence" by UGC Vignana Jyothi Nagar, Pragathi Nagar, Nizampet (S.O), Hyderabad – 500 090, TS, India. Telephone No: 040-2304 2758/59/60, Fax: 040-23042761 E-mail: postbox@vnrvjiet.ac.in, Website: www.vnrvjiet.ac.in



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 - 4.5 UNIT 5 Feedback Amplifiers and Oscillators- WIT Report
 - 4.6 UNIT 6 Special Purpose Semiconductor Devices: WIT Report

5. WIL reports to be submitted by student teams

- 5.1 UNIT 1 PN-Junction Diode and Applications: WIL Report (12-14 reports)
- 5.2 UNIT 2 Bipolar Junction Transistor, Biasing and Stabilization: WIL Report (12-14 reports)
- 5.3 UNIT 3 Field Effect Transistor, Biasing: WIL Report (12-14 reports)

5.4 UNIT 4 Small signal low frequency Amplifiers: BJT Amplifiers: – WIL Report (12-14 reports)

- 5.5 UNIT 5 Feedback Amplifiers and Oscillators WIL Report (12-14 reports)
- 5.6 UNIT 6 Special Purpose Semiconductor Devices: WIL Report (12-14 reports)

1. Syllabus of the Course

Pre-requisites: Engineering Physics

Course Objectives:

- To understand the construction, principle of operation and characteristics of various semiconductor devices.
- To study the applications of various semiconductor devices.
- To have the familiarity with small signal model of semiconductor devices
- To understand the concepts of feedback in amplifiers and Oscillators

Course Outcomes:

After Completion of the course the student will be able to

- 1. Explain the principle of operation and substantiate the applications of various Semiconductor devices.
- 2. Appreciate the need for biasing and stabilization.
- 3. Design the application specific circuits using basic active and passive components
- 4. Explain the necessity of feedback in amplifiers and Oscillators.

UNIT I

PN-Junction Diode and Applications: Review of p-n Junction as a Diode, Diode Equation, Volt-Ampere Characteristics, Temperature dependence of V-I characteristics, Ideal and Practical Diode Equivalent Circuits, Transition and Diffusion Capacitances, Breakdown Mechanisms in Semi-Conductor Diodes, Zener Diode and its Characteristics. Half wave Rectifier, Full wave rectifier, Bridge Rectifier, Harmonic components in a Rectifier Circuit, Capacitor filters, π- section filters, Zener diode as Voltage Regulator.

UNIT II

Bipolar Junction Transistor, Biasing and Stabilization: Bipolar Junction Transistor(BJT), Transistor Current Components, Transistor Construction, BJT Operation, Common Base, Common Emitter and Common Collector Configurations, Limits of operation, BJT as an Amplifier, BJT Specifications. DC and AC Load lines, Quiescent operating point, Need for Biasing, Analysis of Fixed Bias, Collector Feedback Bias, Emitter Feedback Bias, Collector-Emitter Feedback Bias, Voltage Divider Bias, Bias Stability, Stabilization Factors, Stabilization against variations in V_{BE} , Band I_{CO}, Thermal Runaway, Thermal Stability and Compensation Techniques

UNIT III

Field Effect Transistor, Biasing: Construction and operation of Junction Field Effect Transistor (JFET), Volt-Ampere characteristics- Drain and Transfer Characteristics, FET as Voltage Variable Resistor, FET Biasing, Construction and operation of MOSFET, MOSFET characteristics in Enhancement and Depletion modes.

UNIT IV

Small signal low frequency Amplifiers: BJT Amplifiers: Small signal low frequency transistor amplifier circuits: h-parameter representation and analysis of single stage CE, CC, CB

amplifiers - Computation of Voltage gain, Current gain, Input impedance and Output impedance, Comparison of CB, CE, CC amplifiers.

JFET Amplifiers: JFET Small Signal Model, FET Common Source Amplifier, Common Drain Amplifier.

UNIT V

Feedback Amplifiers and Oscillators: Concept of feedback, Types of feedback, general characteristics of negative feedback amplifiers, voltage series, voltage shunt, current series and current shunt feedback configurations and their analysis(BJT version), Illustrative problems.

Classification of oscillators, Conditions for oscillations, RC phase shift oscillator, Generalized analysis of LC oscillators – Hartley and Colpitts oscillators, piezoelectric crystal oscillator, Stability of oscillators.

UNIT VI

Special Purpose Semiconductor Devices: Tunnel Diode, Varactor Diode, Photo Diode, Photo Transistor, UJT, LED, SCR

TEXT BOOKS

1. Electronic Devices and Circuits – J.Millman, C.Halkias, and Satyabrata Jit, 4th Edition, Tata McGraw Hill, 2015.

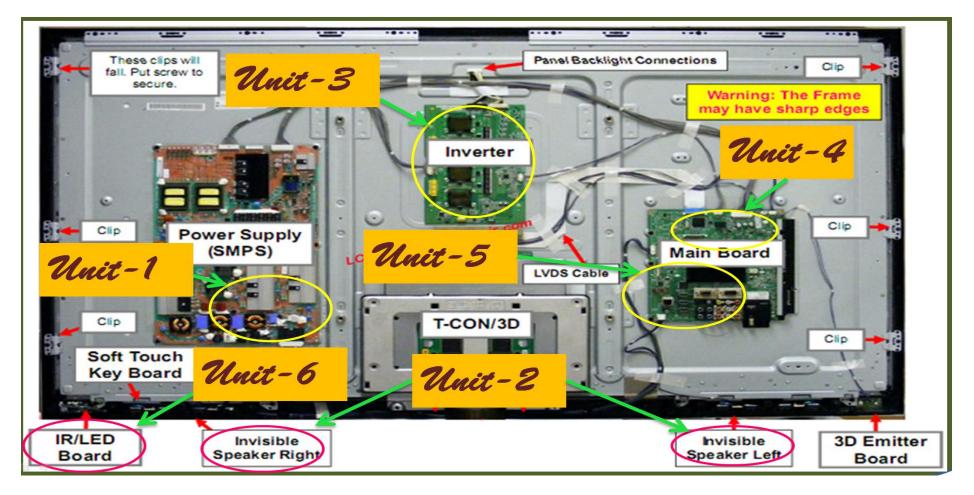
2. Electronic Devices and Circuits – R.L. Boylestad and Louis Nashelsky, 11th Edition, Pearson/Prentice Hall, 2016.

REFERENCES

1. Integrated Electronics - J.Millman ,C.Halkias, and Chetan D Parikh, 2ndEdition,Tata McGraw Hill, 2010.

2. Electronic Devices and Circuits – T.F. Bogart Jr., J.S.Beasley and G.Rico, 6thEdition, Pearson Education, 2004.

3. Microelectronic Circuits- Adel S. Sedra and Kenneth C. Smith 7th edition, Oxford, 2014.



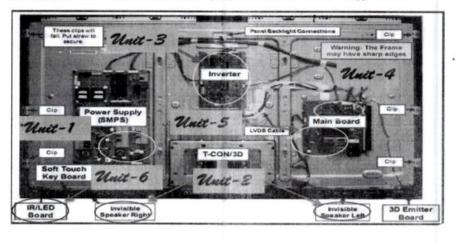
2. Scenario with Industry Endorsement

Fig.1. Internal circuit diagram other PCBs wiring diagram of a LCD/LED TV $\,$

Industry Endorsement

This is to endorse that the following WIT scenario titled "LCD/LED Television Internal Circuit" can be used as a teaching-learning methodology for the subject titled "Electronic Devices and Circuits" for B. Tech II Year Electrical and Electronics Engineering students.

WIT & WIL methodology is a teaching-learning process of VNR VIGNANA JYOTHI INSTITUTE OF ENGINEERING AND TECHNOLOGY which would aim to bridge the gap between institutional academic systems and industry requirements. The definition of "WIT & WIL" method explained as an active methodology of teaching and learning activity with "Why am I Teaching" and "What am I Teaching" from Teacher's perspective and "Why am I Learning" and "What am I Learning" from students perspective. The taken scenario resembles the application of electronic devices studied part of academic with real time applications.



2 Stamp / Signature of Endorsing Industry

Stamp / Signature of Endorsing Industry प्रवेधक (संचार) Manager (COM) भारतीय विमानपत्तन प्राधिकरण AIRPORTS AUTHORITY OF INDIA वे.स.के निर्फ्यात हवाईआडडा A.C.S., Tirupati Airport

3. Brief Explanation of the Scenario

The scenario chosen to explain WIT & WILTM is that of a typical internal circuit and wiring diagram of a LCD/LED television which encompasses most of the topics and subtopics of the syllabus for R19 regulation of Electronic devices and circuits for Undergraduate students of Electrical and Electronics Engineering.

Introduction to the scenario and the subject

Liquid crystal display (LCD) and light emitting diode (LED) technology have been using these days for display applications. Consumer electronics are become more demands and Television, advertising board and monitors or displays are using this technology in very wide range.

A generic layout and internal circuit diagram and wiring diagram of an LCD/LED TV have been shown in Figure.1. An LCD/LED television is a complex circuit consisting of various components to display an image on screen. On observation, one realises that there are various components in the scenario such as power supply unit, inverter, main controller board,

Most of these components are noticed in each circuits is a combination of various electronic devices such as diodes, transistors, feedback amplifiers and few special kind of devices. Each printed circuit board showed in Fig.1 performs specific task like it takes different types of inputs and are processed to get desired output on the screen with audio. The basic characteristics of various electronic devices performed in each circuit to generate the required output.

The components described here can also be seen in various other electronics and electrical projects like mobile phone, communication based train control (CBTC), chargers and refrigerators and elevators. The contents of the subject help one to understand the problems encountered, the science governing the problem and tools to design solutions to problems encountered in displaying picture on screen on interfacing multiple devices parallel.

The scope of this subject is very wide and the concepts of this subject can be used in development of control circuits in consumer electronics, industrial, commercial, medical and defence sectors. In battery charging applications electronics circuit plays an important in governing charge feeding to battery, temperature at battery terminals, voltage control and charging time etc.

Relevance of the scenario to the syllabus

Let's analyze the circuit shown in Fig.1 and relate them with electronic device characteristics and their application starting from unit 1 to unit 6. The present technology using LCD/LED televisions are having multiple input ports such as satellite signal, HDMI, Ethernet, VGA, USB and control signal from remote etc. The various input signals received from various input ports processed by different electronic devices present in PCBs. Printed circuit boards (PCBs) shown in Fig.1 performs various task on utilizing various electronic devices such as p-n junction diode, bi-polar junction transistor (BJT), field effect transistor (FET) and few special devices like Light emitting diodes, photo diode, photo transistor, varactor diode and uni-junction transistor(UJT).

The basic semi conductor element p-n junction diode and zener diode characteristics and their applications are found in unit -1 which relates with power supply (SMPS) board in scenario. This power supply board will provide power to all PCBs and to other components which needs power. Power supply card takes AC input and stepped down with the help of transformer and later it converts into DC by using p-n junction diodes. That DC power supplied to all PCBs and ICS etc. Some places where needs to be maintain constant voltage in which zener diodes will be used and will act as voltage regulators.

As present TVs takes multiple inputs and are processed using few circuits the video will be displayed on the screen, but the audio for the same should be delivered through amplifier. The signal received from various sources will have very low in magnitude. The same cannot be delivered to the output. But, the signal strength can be increased using amplifier circuits. The speaker section along with amplifier shown in scenario can be mapped with unit-2. Since here we study the characteristics of BJT in differenternt configuration and can be used for amplifier application.

Signals are of different types like video and audio signals, these signals are feeded into various electronic circuits through various input modes. Sometimes signals received from satellite, sometimes HDMI ports or sometimes wifi module etc. Few devices need AC signals, but from source (Power supply) card we get only DC. So, needs a circuit which converts DC into AC. The circuit which converts DC into AC is called inverter, wherein controlled switches such as MOSFETs will be used and are operated at very high frequencies. In unit-3 will study the characteristics of field effect transistors and their applications, so in scenario the inverter can be mapped with unit-3.

Scenario shown in Fig.1 consists a major circuit board named main board. It has numerous components and is used to perform different tasks. Circuits embedded on to this board consist of semiconductors p-n junction diodes, transistors and special devices. To implement any circuit one has to analyze the circuit by replacing all devices with their equivalent circuits. On replacement on can find various parameters like input resistance, output resistance, voltage gain and current gain. Analysis can be done using h-parameters approach and it can be done easy by using small signal analysis of BJT and FET. The processor can perform operation based on the clock signal generated in the circuit.

Positive feed-back circuits are capable of generating different forms of signals; such signal can be fed to the processor to perform activities. Clock pulses of square wave can be generated using multivibrators. An astable multivibrator used to generate continuous square wave with a frequency. A crystal oscillator is used for this application. In most of the times processor takes feedback signal and is processed. So, unit-4 and uni-5 mapped with this main board which covers topics of small signal modelling of fourth unit and feedback concepts of unit fifth.

Special kind of devices is used in many industrial and consumer electronics. Devices such as UJT (Uni junction transistors), SCR (Silicon controlled rectifiers), LED (Light emitting diode and photo transistors and etc. In this scenario uni-6 mapped with LED panel or LCD panel and which is special kind of device can be used for display applications. Even SCR can be used to get control on power supply in converting ac to dc.



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Course Na	me	Electronic Devices and Circuits		Year/ Seme	ester		II BTECH /I SEMESTER (AY 2020-2021)			
Course Co	de	19PC1EC02		Scenario Er	ndorsing Industry a	& Logo	Airports authority of India			
Name of t	he Faculty	Dr. Pasula Naresh								
		4.1	INTEGRATION OF SYLLAB	SUS, WIT & W	IL [™] SCENARIO AN	ID TEACHIN	G PLAN			
	WIT & WI			Mapping		ſ	Teaching p	lan	1	
Lecture No.	Contents of the syllabus				Lecture Dates*	Deli	very Methodologies	Learning Resources / References	Course Outcomes	
1	Scenario explanation LCD/LED Televis		LCD/LED Television and circuit	l its internal	17.08.2020		DM8 (S)	L1	CO-1,2,3,4	
Brief Desc	ription of WIT: The tak	ken scenario (i.e. LCD/LED TV inter	nal circuit) resembles the a	pplication of	various electronic	devices and	I how they will be used to a	achieve a particular outpu	ut. Television or	
display bo	ards are used to displa	y an image or play videos.								
Unit 1: Stu	idy of PN-Junction Diod	de characteristics plays an importa	nt role in choosing this dev	vice to differer	nt applications in e	lectronic ci	rcuits wherein one has to t	focus device characteristi	cs and ratings.	
Especially	in AC-DC conversion in	n fundamental frequency and high i	frequency applications							
Unit 2: Bia	sing and stabilization p	plays an important role in application	ons where BJT can be used	as a switch, a	mplifier and regul	ating device	e. The transistor paramete	rs study while studying it:	s characteristics in	
different c	onfigurations enable d	lesigners to shoes this device for di	fferent applications.							
Unit 3: The	e chip size decreased to	o a very low level because of this d	evice, wherein on study th	e characterist	ics of this device a	nd can able	to explore this device for	various industrial and co	ntrolling circuits.	
Microproc	essor and switched mo	ode power supply uses these devic	es as a fast switching devic	æ.						
Unit 4: De	signing any electronic o	circuit to perform certain operation	n need to be analyzed in de	etail. It is only	possible when ead	ch of electro	onic devices replaced with	its equivalent circuit diag	ram and solving for	
various pa	rameters such as volta	ge and current gain and input and	output impedances.							
Unit 5: A c	Unit 5: A closed loop system preferred in most cases where a precise and accurate control over parameters such as voltage and currents. Feedback circuits like +ve and –ve amplifiers are used to control and									
	generated a kind of waveforms. Basically the feedback circuits are fed by output signal and they amplified to a level then they compared with reference signal.									
0		ill be done by normal p-n junction (,			•	5	evices. Those operations	may be done with	
	o .	ations like –ve resistance, display,		•			0	·	,	

		UNIT 1: P-N Junction diode	and applications	(S.1)		
		Mart - 6 Mart - 6 Mar		Cip Power Supply (SMPS) Cip Over Supply (SMPS)		
1.	Review of p-n Junction as a Diode	Converticut Convert Prov	18.08.2020	DM1, DM2, DM8 AV1 (S.1.1)	T1,T2,R1R2	CO-1
2.	Diode Equation	Bilicon Discha and An S-1 Cheresteristica S-1 Cheresteristica	20.08.2020	DM1, DM4,DM8, AV1 (S.1.1)	T1,T2,R1R2	CO-1,3
3.	Volt-Ampere Characteristics, Temperature dependence of V-I characteristics,		24.08.2020	DM1,DM2, DM4,DM8, AV2 (S.1.1)	T1,T2,R1R2	CO-1
4.	Ideal and Practical Diode Equivalent Circuits, Transition capacitance	V ₂₀₀	25.08.2020	DM1, DM8,AV2 (S.1.1)	T1,T2,R1R2	CO-1, 3
5.	Diffusion Capacitances	V _{au}	27.08.2020	DM1, DM8,AV2 (S.1.1)	T1,T2,R1R2	CO-1,3
230V and into DC po	cription of WIT: There are two types of power supplies of 50 Hz for domestic applications. But, this power cannot b ower is so called rectifier. In which uncontrolled or someti nd the device here it is a p-n junction diode. Here will stud	be used for electronic circuits, since the mes controlled semiconductor devices	y work for low vo	ltages and that too it is a DC power. A cased on requirement. The scenario conne	circuit that can be use	d to convert AC power
6.	Breakdown Mechanisms in Semi-Conductor Diodes	Bridge Restlar Di	31.08.2020	DM1, DM4, DM8, AV3(S.1.2)	T1,T2,R1	CO-2,3
7.	Zener Diode and its characteristics.	Dy by Capacitor Ov	01.09.2020	DM1,DM2, DM8, AV3 (S.1.2)	T1,T2,R1	CO-1,2,3
8.	Half wave Rectifier	Peppier C Charges C Discourges Wereform units C Charges C Discourges With C Capacity Vec Capacity OV V V V V V V V V V V V V V V V V V V	03.09.2020	DM1, DM8 (S.1.2)	T1,T2,R1	CO-2,3
9.	Full wave rectifier, Bridge Rectifier	Hermuthant. Contract. Monverform. + → → R → B → + + + + + + + + + + + + + + + + +	07.09.2020	DM1, DM8 (S.1.2)	T1,T2,R1	CO-1, 2
10.	Harmonic components in a Rectifier Circuit	Unregulated Vz Regulated Input Vin Vo	08.09.2020	DM1, DM4, DM8, AV4(S.1.2)	T1,T2,R1	CO-3
11.	Capacitor filters, π - section filters and Zener diode as Voltage Regulator.		10.09.2020	DM1,DM2, DM4,DM8, AV3 (S.1.2)	T1,T2,R1	CO-1,2,3
Brief Desc	ription of WIT: In the process of converting AC-DC one h	as touse either p-n junction diode or if	a variable DC nee	ded then one has to use controlled devi	ce. A single diode is ι	sed to convert into DC

or one can use two or four for higher average output. The output obtained here is a pulsated DC and whose ripples should be removed. There are different types of filters which will be used to remove ripples in current and voltage. A L-filter is used to remove ripples in current, a C-filter is used to remove ripples in voltage and an LC and CLC filters are used to remove ripples both in current and voltage. In some situation one has to maintain constant DC supply voltage for ICs and other electronic devices. Zener diodes are useful in this regard. The scenario covers bother devices p-n junction diode and zener diode applications.

12.	Tutorial	Applications of diodes & Application	14.09.2020	DM1, DM8 (S.1)	T1,T2,R1,R2	CO-1,3				
13.	Tutorial	of zener as voltage regulator	15.09.2020	DM1, DM4,DM8,,AV1,AV4 (S.1)	T1,T2,R1,R2	CO-1,3				
Related Do	Related Documents:									
1. Syllabus	of the course as defined in the curriculum – Fluid Mecha	nics								
2. Academ	ic plan & teaching plan									
3. WIT&WI	IL™ Scenario Endorsement									
Details of Delivery Methodologies used: DM1: Chalk and Talk DM2: Learning by doing DM4: Demonstration (Physical / Laboratory / Audio Visuals / PPT) DM6: Case Study (Work on real data) DM8: WIT & WIL Audio Visuals: AV1 - P-N Junction diode formation https://www.youtube.com/watch?v=0yyFiJwSemw&t=2s AV2 - P-N Junction diode characteristics https://www.youtube.com/watch?v=0yC02DWq3ml&t=215s AV3 - P-N Junction diode applications https://www.youtube.com/watch?v=0yC02DWq3ml&t=215s AV3 - P-N Junction diode applications https://www.youtube.com/watch?v=0yC02DWq3ml&t=215s AV3 - P-N Junction diode applications https://www.youtube.com/watch?v=1BtEckh3190 AV4 - Zener diode applications https://www.youtube.com/watch?v=1BtEckh3190 AV4 - Zener diode applications https://www.youtube.com/watch?v=Fwi d3uO5g8 PowerPoint Presentation: PPT - https://drive.google.com/file/d/1bM2lYHen1Z_XHpsT3LmLxwdsqPm3oSXv/view?usp=sharing										
Physical Demonstrations: P1 – Demonstration with different types of P-N junction diode and Zener diode										
P2	P2 – Demonstration through experiment P-N Junction diode and full wave rectifier									



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Course Na	ame	Electronic Devices and Circuits		Year/ Semest	er		II BTECH /I SEMESTER (AY 2	020-2021)	
Course Co	ode	19PC1EC02	Scenario Endorsing Industr		orsing Industry &	Logo Airports authority of India			
Name of t	the Faculty	Dr. Pasula Naresh							
		4.	2 INTEGRATION OF SYLLAB	US, WIT & WI	L [™] SCENARIO AN	D TEACHIN	G PLAN		
			WIT & WIL Scenario I	Mapping			Teaching pla	in	
Lecture No.	Cont	ents of the syllabus			Lecture Dates*	Del	ivery Methodologies	Learning Resources / References	Course Outcomes
			UNIT 2: Bipolar Junctio	on Transistor, I	Biasing and Stabili	zation: (S.2	:)		
		Content Content Service Content Conten	Provide and the second	Mant - 4 Mant - 4 Car Car Car Car Car Car Car Car	Unit-d	2	hvisible Speaker Left		
14.	Introduction to unit fluid flows Bipolar Junction Tra Limits of operation,	using WIT & WIL; Description of nsistor(BJT),	BJT Construction and cont	figurations	17.09.2020	DM1, DM	4, DM8,AV1(S.2.1)	T1,T2, R2	CO-2
15.	Transistor Current C Construction,	omponents, Transistor	Telefikaar inclostronity no BT KNE	c + v N T ve	21.09.2020	DM1,DM4	4, DM 8,AV1 (S.2.1)	T1,T2, R2	CO-2
16.	BJT Operation, Com Common Emitter an Configurations,	mon Base, d Common Collector		Configuration	22.09.2020	DM1,DM	2, DM4 , DM8,AV2 (S.2.1)	T1,T2, R2	CO-2,3
17.	BJT as an Amplifier, lines, Quiescent ope	BJT Specifications. DC and AC Load trating point,	Source and the second s	BAA BAA BILAA BILAA INAA BILAA INAA BILAA INAA	24.09.2020	DM1, DM	4, DM8,AV2 (S.2.1)	T1,T2, R2	CO-2,3

Brief Description of WIT: Bi-polar junction transistor is a revolutionary semi-conductor device in the 20th century. Multiple applications can be implemented with the help of BJT. Different configuration in the BJT enables the designers to choose BJT for different applications based on the operating regions. The most popular application of BJT is in amplifying applications in which a weak signal is amplified to a very high level. In the chosen scenario this unit is mapped with the amplifier circuit. It is used to deliver voice in a LCD/LED TV by amplifying a low magnitude signal. Specifications of BJT is important in chosing the device for a particular application and for a particular frequency.

18.	Need for Biasing, Analysis of Fixed Bias,	BJT, DC biasing circuits	28.09.2020	DM1,DM2, DM4, DM8, AV2(S.2.2)	T1,T2, R3	CO-2,3
19.	Collector Feedback Bias, Emitter Feedback Bias,		29.09.2020	DM1, DM8 (S.2.2)	T1,T2, R3	CO-2,3
20.	Collector-Emitter Feedback Bias, Voltage Divider Bias,	A base bias	01.10.2020	DM1, DM4, DM8,AV3(S.2.2)	T1,T2, R3	CO-2,3
21.	Bias Stability, Stabilization Factors, Stabilization against variations in VBE, βand ICO,	B base biss + emitter feedback C base biss + collector feedback D voltage divider	05.10.2020	DM1, DM4, DM8,AV3(S.2.2)	T1,T2, R3	CO-2,3
22.	Thermal Runaway, Thermal Stability and Compensation Techniques	Common Emitter Amplifier (CE)	06.10.2020	DM1, DM4, DM8(S.2.2)	T1,T2, R3	CO-2,3
	ription of WIT: Bi-polar junction transistor operating cond					
	in either active or saturation region. The biasing will prov racteristics and can be nullified partially with stabilizing ci	C C	•	Ū	gion. The temperature va	riation can effect the
uevice cha	racteristics and can be number partially with stabilizing ch	cuits. In the scenario BT is used to ampir	rying action where			
23.	Tutorial	Pump house, pipe network	08.10.2020	DM, DM8 (S.2)	T1,T2,R1, R3	CO-2,3
24.	Tutorial	Inter-2	12.10.2020	DM1, DM4, DM8 (S.2)	T1,T2, R3	CO-2,3
Related Do	ocuments: 1. Syllabus of the course as defined in the cur	riculum – Fluid Mechanics				
2. Academ	ic plan & teaching plan					
3. WIT&W	IL™ Scenario Endorsement					
DM DM DM DM	<u>Delivery Methodologies used:</u> 1: Chalk and Talk 2: Learning by doing 4: Demonstration (Physical / Laboratory / Audio Visuals , 6: Case Study (Work on real data) 8: WIT & WIL	/ РРТ)				
	lio Visuals: '1 – Streamline, Streakline, Pathline <u>https://www.youtube</u>	.com/watch?v=flvZen2tq_w_				

AV2 – Flownet https://www.youtube.com/watch?v=7ukDKVHnac4

AV3 – Continuity equation <u>https://www.youtube.com/watch?v=-VwPSDQmdjM</u>

PowerPoint Presentation:

PPT - https://drive.google.com/file/d/1bM2IYHen1Z_XHpsT3LmLxwdsqPm3oSXv/view?usp=sharing

Physical Demonstrations:

P1 – Demonstration with different types configuration in BJT and parameter calculation from input and output characteristics

P2 – Demonstration through experiment CE configuration as amplifier



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ourse Name	Electropic Dovices and Circuits							
urse Name Electronic Devices and Circuits			Year/ Semest	ter		II BTECH /I SEMESTER (AY 2	2020-2021)	
ourse Code	19PC1EC02	19PC1EC02		Scenario Endorsing Industry & Logo		Airports authority of India		
ame of the Facul	lty Dr. Pasula Naresh							
		4.3 INTEGRATION OF SYLLAE	BUS, WIT & WI	IL [™] SCENARIO AN	ID TEACHIN	IG PLAN		
		WIT & WIL Scenario	Mapping		-	Teaching pla	an	
ecture No.	Contents of the syllabus				De	livery Methodologies	Learning Resources / References	Course Outcom
		UNIT 3 Fie	ld Effect Trans	sistor, Biasing (S.3	\$)			
	X	Construction Co	Marce-4 Marceard Company Compa			Inverter		
25. Constr	luction to unit using WIT & WIL; ruction and operation of Junction Field Effect istor (JFET)	FET Characteristics		13.10.2020	DM1, DN	Л4, DM8,AV1 (S.3.1)	T1, R1,R2	CO-2,3
26. Volt-A	Ampere characteristics		$\label{eq:constraint} \begin{split} V_{ijk} &= 0.V \\ & V_{ijk} &= 0.V \\ & V_{ijk} &= -1.V \\ & V_{ijk} &= \frac{1}{2}V \\ & V_{ijk} &= \frac{1}{2}V \\ & V \\ & $	15.10.2020	DM1,DN	12, DM8,AV1 (S.3.1)	T1, R1,R2	CO-2,3
27. Drain a	and Transfer Characteristics	$\frac{-\frac{1}{2}}{\frac{1}{2}} \frac{\frac{1}{2}}{\frac{1}{2}} \frac{\frac{1}{2}}{\frac{1}{2}} \frac{1}{\frac{1}{2}} \frac{1}{\frac{1}$	$V_{\rm det}=V_{\rm s}^{-1}-\alpha \cdot V^{-1}$	19.10.2020	DM1,DN	12, DM8 (S.3.1)	T1, R1,R2	CO-2,3
28. FET as	s Voltage Variable Resistor	When $V(u_2)$, $U(k_1)$ is a loss $The formula used to plot the Transfer Carve, is: I == Im \Big\{ 1$	<u>v</u>)'	20.10.2020	DM1, DN	л4, DM8,AV2 (S.3.1)	T1, R1,R2	CO-2,3
rief Description of	of WIT: Microprocessor become popular and the	heir applications in electronic	industry got in	I mportance after ir	nventing fie	eld effect transistor. These tr	ansistors are superior in	many parameters
ompared to BJT. T	These transistors are fast, occupy less space on	chip and had high thermal co-	efficient. Chara	acteristics of FET a	are differen	t from BJT in which output ca	an be controlled in two w	ays. It can also use
ariable resistor. Ir	n this scenario these devices are used to imple	ment inverter circuit, in which	the DC conve	rter into AC by op	erating swi	tches at a frequency based o	on requirement. Switched	l power supplies u
	operated at very high frequency.	, -		, -r	0	, ,		

29.	FET Biasing, Construction and operation of MOSFET,	¥89,15 ¥ ¥00,15 ¥ × ¥00,15 ¥	22.10.2020	DM1, DM4, DM8,AV3(S.3.2)	T1, R1,R2	CO-2,3				
30.	MOSFET characteristics in Depletion modes.	Vel L Flore L for Figure 2. L fail from . Figure 2. L fail from .	26.10.2020	DM1, DM8AV3(S.3.2)	T1, R1,R2	CO-2,3				
31.	MOSFET characteristics in Enhancement		27.10.2020	DM1, DM4, DM8,AV3(S.3.2)	T1, R1,R2	C CO-2,3				
32.	Numerical problems	29.10.2020	DM1, DM4, DM8(S.3.2)	Т1, Т3	CO-2,3					
Brief Descr	Brief Description of WIT: Biasing is needed even in FET, since it has three operating regions similar to BJT and are decided by providing proper biasing. These operating regions are ohmic, cut-off and saturation									
-	OSFET used as switch when it operated in ohmic region a to depletion mode. In this scenario enhancement MOSFET	-			nobility of electrons in	enhance mode is high				
33.	Tutorial	Unit-3	09.11.2020	DM1, DM8 (S.3)	T1, R1,R2	CO CO-2,3				
34.	Assignment test		10.11.2020	DM2,DM4	T1, T2, R1,R2	CO-1,2,3				
35.	Revision of Units 1,2,3	Rear Legar Rear Legar Control Control	12.11.2020	DM2,DM4	T1, T2, R1,R2	CO-1,2,3				
Related Do	cuments: 1. Syllabus of the course as defined in the cu c plan & teaching plan 3. WIT&WIL [™] Scenario Endorseme									
DM: DM: DM4	Delivery Methodologies used: 1: Chalk and Talk 2: Learning by doing 4: Demonstration (Physical / Laboratory / Audio Visuals /	РРТ)								
	6: Case Study (Work on real data) 8: WIT & WIL									
Aud	io Visuals:									
	V1 – FET Characteristics https://www.youtube.com/watch V2 – Biasing and applications of JET and MOSFET https://w)							
AV3 – Power converters: <u>https://www.youtube.com/watch?v=ilqhAX017ll</u>										
PowerPoint Presentation: PPT - https://drive.google.com/file/d/1bM2IYHen1Z_XHpsT3LmLxwdsqPm3oSXv/view?usp=sharing										
Physical Demonstrations:										
P1 -	Demonstration with different types CS configuration and	parameter calculation from input and ou	tput characteristic	S						

	Approve Vignan Estd.1995	INSTITUTE OF ENGINEERING 9001:2015 & QS I-Gauge Diamond Rat NBA Accreditation for CE, EEE, ME, ECE d by AICTE, New Delhi, Affiliated to JNTI Recognized as "College with Pote a Jyothi Nagar, Pragathi Nagar, Nizam Telephone No: 040-2304 2758/ E-mail: postbox@vnrvjiet.ac.in, V	VALURUPALLI NAGESWARA RAO VIGNANA JYOTHI INSTITUTE OF ENGINEERING AND TECHNOLOGY D1:2015 & QS I-Gauge Diamond Rated Institute, Accredited by NAAC with 'A++' Grade A Accreditation for CE, EEE, ME, ECE, CSE, EIE, IT B.Tech. Programmes (AICTE, New Delhi, Affiliated to JNTUH, NIRF 109 Rank in engineering Category Recognized as "College with Potential for Excellence" by UGC othi Nagar, Pragathi Nagar, Nizampet (S.O), Hyderabad – 500 090, TS, India. Telephone No: 040-2304 2758/59/60, Fax: 040-23042761 E-mail: postbox@vnrvjiet.ac.in, Website: www.vnrvjiet.ac.in				
Course Na		Year/ Semest		II BTECH /I SEMESTER (AY 2 IVRCL Pvt. Ltd.	(019-2020)		
Course Co		Scenario End	orsing Industry &	Logo	WAREL		
Name of t	he Faculty Keerthi Priya Kasturi	4.4 INTEGRATION OF SYLLABUS, WIT & WI	L [™] SCENARIO AN	D TEACHING PLAN			
		WIT & WIL Scenario Mapping		Teaching pla	an		
Lecture No.	Contents of the syllabus		Lecture Dates*	Delivery Methodologies	Learning Resources / References	Course Outcomes	
		Aude-S Aude-S		Warning: The Frame may have sharp edges			
36.	Introduction to unit using WIT & WIL; Small signal low frequency transistor amplifier circu parameter representation	its: h	16.11.2020	DM1 ,DM4 , DM8,AV1 (S.4.1)	T1, T2,R2,R3	CO-3	
37.	Analysis of single stage CE, CC, CB amplifiers, Computation of Voltage gain, Current gain		17.11.2020	DM1, DM8,AV1 (S.4.1)	T1, T2,R2,R3	CO-3	
38.	Input impedance and Output impedance, Comparis of CB, CE, CC amplifiers.	on $\frac{k_{1}}{k_{1}} = g_{11} \vee k_{2}$ $k_{2} = g_{11} \vee k_{2}$ $k_{3} = h + k_{2}$ $k_{4} = g_{11} \vee g_{12}$ $k_{4} = g_{11} \vee g_{12}$ $k_{5} = g_{12} \vee g_{12}$	19.11.2020	DM1,DM2, DM8,AV1 (S.4.1)	T1, T2,R2,R3	CO-3	

Brief Description of WIT: To design any electronic circuit to implement a particular operation one should have knowledge for which kind load the circuit is designing and for value of load it is implementing. So, these electronic circuits can be designed by using transistors only when the designer has the knowledge of equivalent circuit of semiconductor device which we are using. At the same time what are different parameters is used to define the equivalent circuit. In general transistors are chosen based on the gain provided by transistor such as voltage , current gains and input and output impedances. In this scenario it is mapped with main control circuit board where different transistor for different applications.

39.	JFET Small Signal Model Amplifier	Small signal model of FET	24.11.2020	DM1,DM8,AV2 (S.4.2)	T1, T2,R2,R3	CO-3
40.	FET Common Source Common Drain Amplifier	vesteng g g ve provide state s	30.11.2020	DM1,DM2,DM8,AV2 (S.4.2)	T1, T2,R2,R3	CO-3
Brief Desc	ription of WIT: Field effect transistors are also used as vol	ltage variable resistor. This feature enabl	es the designers to	o chose this device as a resistor instead	of a normal resistor. This	s can be modelled as
variable re	sistor only when its equivalent circuit and also its input an	d out resistances offered by the device. S	mall signal modell	ling helps in designing this resistor. In th	is scenario it is mapped v	vith electronic circuit
in the main	n board PCB to use FET as a variable resistor.					
41.	Tutorial	Reference The Part of the Part	01.12.2020	DM1, DM8	T1, T2,R2,R3	CO-3
	Related D	ocuments: 1. Syllabus of the course a	s defined in the cu	rriculum – Fluid Mechanics		
2. Academ	ic plan & teaching plan					
		3. WIT&WIL [™] Scenario End	lorsement			
Details of	Delivery Methodologies used:					
DM DM DM A A Pov PP	1: Chalk and Talk 2: Learning by doing 4: Demonstration (Physical / Laboratory / Audio Visuals / 6: Case Study (Work on real data) 8: WIT & WIL V1 – <u>https://www.youtube.com/watch?v=i2t9GTAd2I0</u> V2 – <u>https://www.youtube.com/watch?v=NESchIntkR8</u> werPoint Presentation: T - <u>https://drive.google.com/file/d/1bM2IYHen1Z_XHpsT3</u> reicel Demonstrations:					
	rsical Demonstrations: Demonstration of CE and CB Transistor configuration to figuration 	ind design parameters				

Course Nai Course Course Cours	N Approved to Vignana . Estd.1995 me Fluid Mechanics	VALLURUPALLI NAGESWARA INSTITUTE OF ENGINEERING 001:2015 & QS I-Gauge Diamond Rat BA Accreditation for CE, EEE, ME, EC by AICTE, New Delhi, Affiliated to JNT Recognized as "College with Pote Jyothi Nagar, Pragathi Nagar, Nizam Telephone No: 040-2304 2758, E-mail: postbox@vnrvjiet.ac.in, W Year/ Semes Scenario End	AND TECHNOL ed Institute, Ac. E, CSE, EIE, IT B.T UH, NIRF 109 Ra ential for Excelle pet (S.O), Hyde /59/60, Fax: 040 Vebsite: www.v	COGY credited by NAAC with 'A++' Gr ech. Programmes nk in engineering Category nce" by UGC rabad – 500 090, TS, India. -23042761 nrvjiet.ac.in II BTECH /I SEMESTER (AY	Promoting Excellence	STOTHI INSTITUTE DE CONTRACTOR				
Name of th	• •	4.5 INTEGRATION OF SYLLABUS, WIT & W	IL™ SCENARIO AN	D TFACHING PLAN						
	4.5 INTEGRATION OF STELABOS, WIT & WIL SCENARIO AND TEACHING PLAN WIT & WIL Scenario Mapping Teaching plan									
Lecture No.	Contents of the syllabus		Lecture Dates*	Delivery Methodologies	Learning Resources / References	Course Outcomes				
	En	And a state of the	t-con/3D	LVDS Cable						
42.	Introduction to unit using WIT & WIL; Concept of feedback		03.12.2020	DM1, DM8,AV1 (S.5.1)	T1,R1,R3	CO-4				
43.	Types of feedback, general characteristics of negative feedback amplifiers	Vi Free taak Vi	07.012.2020	DM1, DM8,AV1 (S.5.1)	T1,R1,R3	CO-4				
44.	current series and current shunt feedback configurations and their analysis(BJT version)	Voltage series feedback Vin Vin OP. AMP Field tank Current series feedback Current series feedback	08.12.2020	DM1, DM8,AV2 (S.5.1)	T1,R1,R3	CO-4				
	ription of WIT: Feedback circuits play an important role i			-						
	g the circuit output on comparing with reference input.			•		U U				
	some cases its added and in some cases it is deducted fr		output to near to	the desired output. In the taken scena	rio it is mapped with main	control circuit board				
wherein te	eedback circuits implemented with transistors to minimiz	e the error signal.								

						-
45.	Classification of oscillators, Conditions for oscillations, RC phase shift oscillator, Generalized analysis of LC oscillators		10.12.2020	DM1,DM4,DM8,AV2 (S.5.2)	T1,R1,R3	CO-4
46.	Hartley and Colpitts oscillators		14.12.2020	DM1, DM8,AV3(S.5.1)	T1,R1,R3	CO-4
47.	Piezoelectric crystal oscillator, Stability of oscillators.		15.12.2020	DM1, DM8,AV3(S.5.1)	T1,R1,R3	CO-4
Brief Desc	ription of WIT: To perform operations at some speed will	be be decided by the sped of the proces	sor. Processor spe	ed depends on the cloak signal. The o	cloak signal continuously p	rovides some kind of
triggering	signal to the processor. These cloak signals are generated i	n the circuit boards with the help of posit	tive feedback circu	uits. These circuits generate square wa	we kind of waveform with	out any input. In such
cases wher	re oscillator circuits will be used for cloak generation. In thi	s scenario it is mapped with main circuit	board a centralize	d processor is used and it is operated	with some frequency. This	frequency is decided
	llator circuit.					
48.	Tutorial		17.12.2020	DM1, DM8 (S.5.2)	Т1, Т2, Т3	CO-4
Related Do	cuments: 1. Syllabus of the course as defined in the cu	rriculum – Fluid Mechanics	I	L		
2. Academ	ic plan & teaching plan					
3. WIT&WI	IL [™] Scenario Endorsement					
	Delivery Methodologies used:					
	1: Chalk and Talk					
DM DM	2: Learning by doing 4: Demonstration (Physical / Laboratory / Audio Visuals / 6: Case Study (Work on real data) 8: WIT & WIL	РРТ)				
	lio Visuals:					
	V1 – <u>https://www.youtube.com/watch?v=4HdsZ1yz_vY</u> V2 – <u>https://www.youtube.com/watch?v=xMCdoFFbto0</u>					
	V3 – <u>https://www.youtube.com/watch?v=hU8zx0RGJGQ</u>					
	<pre>verPoint Presentation: T - https://drive.google.com/file/d/1bM2lYHen1Z_XHpsT3l</pre>	LmLxwdsqPm3oSXv/view?usp=sharing				
,	sical Demonstrations: - Demonstration of –ve and +ve feedback amplifiers throug	h laboratory experiment				

TAMASOMA JYOTHRGAMAYA E-mail: postbox@ynrvijet.gc.in, Website: www.ynrvijet.gc.in							STOTHI INSTITUTE OF THE DECEMBER OF THE DECEMB
Course Coo	de	18PC1CE02	•	orsing Industry &	IVRCI Pvt 1td	in the second	
Name of th	he Faculty	Keerthi Priya Kasturi				Paradologi and Ante	
	[4.6 INTEGRATION OF SYLLABUS, WIT & WI	L [™] SCENARIO AN]
Lecture No.		Contents of the syllabus	WIT & WIL Scenario Mapping	Lecture Dates*	Teaching p Delivery Methodologies	Learning Resources / References	Course Outcomes
			Image: Constraint of the second of the se	Soft Tou Key Board			
49.		o unit using WIT & WIL; Varactor Diode	PHOTOTRANSISTOR Principied Generation, Characteristics, Applications	22.12.2020	DM1, DM8,AV1,AV2,PPT (S.6.1)	T1	CO-1,3
50.	Photo Diode, P	Photo Transistor	Ande Cathole Tunnel diode symbol	24.12.2020	DM1, DM8,AV1,AV2,PPT (S.6.1)	T1, T2, T6	CO-1,3
electronics	and industrial e	lectronics. Regular p-PN junction diodes	e used for special applications such as circui and transistors will not fulfil the need. Spec enario it this unit is mapped with LCD and o	cial fabrication tec	hniques have been used to fabricate sp		

51.	UJT and LED, SCR		28.12.2020	DM1, DM8,AV1,AV2,PPT (S.6.2)	Т1,Т2,Т6	CO-1,3
Brief Desc	ription of WIT: Light emitting diodes, Uni junction transi	stor and silicon controlled rectifiers will	be used for displa	y application, negative resistance applic	ations and generation o	f waveforms and for
controlled	outputs. In the chosen scenario this unit is mapped with L	CD and other circuits wherein it displays a	n output on scree	n and for voltage control applications		
52.	Assignment test and		29.12.2020	DM1, DM3, DM8 (S.6)	T1,T3	CO-1,3
53.	Revision 4,5 and 6, Model question paper discussion	Contraction of the second seco	31.12.2020	DM1, DM8 (S.4,S.5,S.6)	Т1,Т3	CO-1,3,4
Related Do		urriculum – Fluid Mechanics				
	2. Academic plan & teaching plan					
3. 1011 & 101	L [™] Scenario Endorsement					
DM DM DM DM Auc A Pow PP Phy	Delivery Methodologies used: 1: Chalk and Talk 2: Learning by doing 4: Demonstration (Physical / Laboratory / Audio Visuals / 6: Case Study (Work on real data) 8: WIT & WIL lio Visuals: V1 – https://www.youtube.com/watch?v=ZOOUofPeSYY V2 – https://www.youtube.com/watch?v=OAgPUikpvpM verPoint Presentation: T - https://drive.google.com/file/d/1bM2lYHen1Z_XHpsT3 sical Demonstrations: - Demonstration of UJT and special devices through labora	LmLxwdsqPm3oSXv/view?usp=sharing				



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Why am I Teaching What I am Teaching? and Why am I Learning What I am Learning?

5. WIL REPORT

B.TECH. II YEAR II SEMESTER - EEE - B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 1:
		PN-Junction Diode and Applications: Review
		of p-n Junction as a Diode, Diode Equation,
		Volt-Ampere Characteristics, Temperature
		dependence of V-I characteristics, Ideal
		and Practical Diode Equivalent Circuits,
		Transition and Diffusion Capacitances,
		Breakdown Mechanisms in Semi-
		Conductor Diodes, Zener Diode and its
		Characteristics. Half wave Rectifier, Full
		wave rectifier, Bridge Rectifier, Harmonic
		components in a Rectifier Circuit, Capacitor
		filters, π - section filters, Zener diode as
		Voltage Regulator.

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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5. WIL REPORT

B.TECH. II YEAR II SEMESTER – EEE –B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 2:
		Bipolar Junction Transistor, Biasing and
		Stabilization: Bipolar Junction
		Transistor(BJT), Transistor Current
		Components, Transistor Construction, BJT
		Operation, Common Base, Common
		Emitter and Common Collector
		Configurations, Limits of operation, BJT as
		an Amplifier, BJT Specifications. DC and AC
		Load lines, Quiescent operating point,
		Need for Biasing, Analysis of Fixed Bias,
		Collector Feedback Bias, Emitter Feedback
		Bias, Collector-Emitter Feedback Bias,
		Voltage Divider Bias, Bias Stability,
		Stabilization Factors, Stabilization against
		variations in VBE, Band ICO, Thermal
		Runaway, Thermal Stability and
		Compensation Techniques

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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5. WIL REPORT

B.TECH. II YEAR II SEMESTER – EEE –B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 3:
		Field Effect Transistor, Biasing:
		Construction and operation of Junction
		Field Effect, Transistor (JFET), Volt-Ampere characteristics- Drain and Transfe
		Characteristics, FET as Voltage Variable
		Resistor, FET Biasing, Construction and
		operation of MOSFET, MOSFET characteristics in Enhancement and
		Depletion modes.

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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5. WIL REPORT

B.TECH. II YEAR II SEMESTER – EEE – B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 4: Small signal low frequency Amplifiers: BJT Amplifiers: Small signal low frequency transistor amplifier circuits: h-parameter representation and analysis of single stage
		CE, CC, CB amplifiers - Computation of Voltage gain, Current gain, Input impedance and Output impedance, Comparison of CB, CE, CC amplifiers. JFET Amplifiers: JFET Small Signal Model, FET Common Source Amplifier, Common Drain Amplifier.

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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Why am I Teaching What I am Teaching? and Why am I Learning What I am Learning?

5. WIL REPORT

B.TECH. II YEAR II SEMESTER – EEE –B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 5:
		Feedback Amplifiers and Oscillators
		Concept of feedback, Types of feedback,
		general characteristics of negative
		feedback amplifiers, voltage series, voltage
		shunt, current series and current shunt
		feedback configurations and their
		analysis(BJT version), Illustrative problems.
		Classification of oscillators, Conditions for
		oscillations, RC phase shift oscillator,
		Generalized analysis of LC oscillators

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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E-mail: postbox@vnrvjiet.ac.in, Website: www.vnrvjiet.ac.in



Why am I Teaching What I am Teaching? and Why am I Learning What I am Learning?

5. WIL REPORT

B.TECH. II YEAR II SEMESTER – EEE –B

Course Name: Electronic devices and circuits (EDC)

Course Code: 19PC1EC02

Roll No.	Name	Unit – 6:	
		Special Purpose Semiconductor Devices:	
		Tunnel Diode, Varactor Diode, Photo	
		Diode, Photo Transistor, UJT, LED, SCR	

Question 1. What did you learn from this unit?

(Note: This should not reflect the syllabus of the lesson. Student is required to write in his/her own words the learning outcome of this unit)

ANSWER 1:

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

ANSWER 2:

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



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Why am I Teaching What I am Teaching? and Why am I Learning What I am Learning?5. *Sample* WIL REPORT

B.TECH. II YEAR I SEMESTER – CE – A

Course Name: FLUID MECHANICS

Course Code: 18PC1CE02

Roll No.	Name	Unit – 1: PN-Junction Diode and Applications: Review	
19071A0201	ABC	of p-n Junction as a Diode, Diode Equation, Volt-Ampere Characteristics, Temperature	
19071A0202	ABC	dependence of V-I characteristics, Idea and Practical Diode Equivalent Circuits	
19071A0203	ABC	Transition and Diffusion Capacitance Breakdown Mechanisms in Sem Conductor Diodes, Zener Diode and i Characteristics. Half wave Rectifier, Fu wave rectifier, Bridge Rectifier, Harmon components in a Rectifier Circuit, Capacito	
19071A0204	ABC		
19071A0205	ABC	filters, π - section filters, Zener diode as Voltage Regulator.	

Question 1. What did you learn from this unit?

- 1. Physics behind formation of P-N junction diode
- 2. V-I characteristics and temperature dependence of P-N junction diode
- 3. Application of P-N junction diode
- 4. Differences between half wave and full wave rectifier
- 5. Zener diode formation characteristics in reverse biased condition
- 6. Zener as voltage regulator

Question 2: Was the application illustrated clear for your understanding of the topics covered in this unit? (Explain in few words)

The formation of P-N junction diode and its characteristics explained on taking temperature reference. Application of P-N junction diode in the conversion of AC-DC illustrated through demonstration. How zener regulates the voltage across load explained in detail.

Question 3: Identify and explain an additional/new application to illustrate your understanding of the topics covered in this unit.



Diodes are used in converting one form of energy into another form. The average output can be different in different types connections such as half wave and full wave rectification. Zener operated in reverse biased condition to regulate the voltage across load even when resistance of the load is varied.